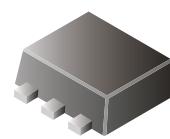


Dual P-Channel MOSFET

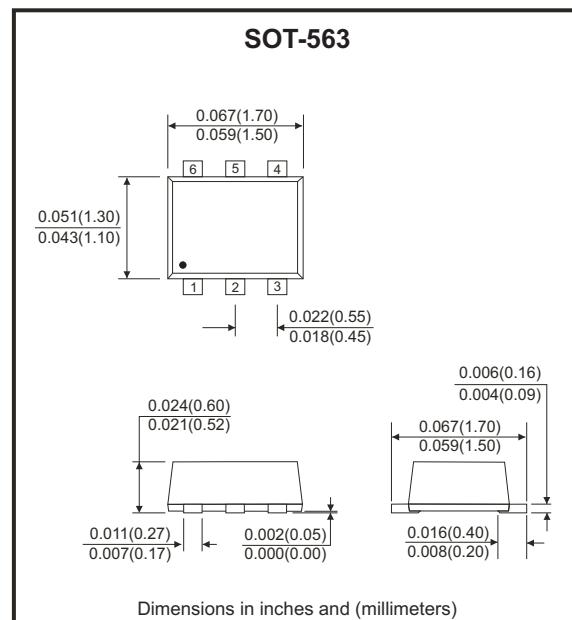
Comchip
SMD Diode Specialist

CJX3139K-G

P-Channel RoHS Device



V(BR)DSS	RDS(on)MAX	ID
-20V	520mΩ@-4.5V	-0.66A
	700mΩ@-2.5V	
	950mΩ(Typ.)@-1.8V	



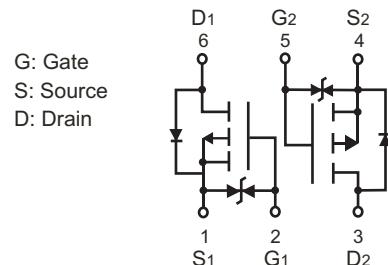
Features

- High-side switching.
- Low on-resistance.
- Low threshold.
- Fast switching speed.

Mechanical data

- Case: SOT-563, Molded Plastic
- Terminals: Solderable per MIL-STD-750,
Method 2026.

Circuit diagram



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-source voltage	V _{DSS}	-20	V
Typical gate-source voltage	V _{Gs}	±12	V
Drain current-continuous	I _D (DC)	-0.66	A
Drain current-pulsed (Note 1)	I _{DM(pulses)}	-2.64	A
Power dissipation (Note 2)	P _D	150	mW
Thermal resistance from junction to ambient	R _{θJA}	833	°C/W
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55 to +150	°C

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at Ta=25°C.

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REV: A

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
On/Off States						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V , I _D =-250μA	-20			V
Gate threshold voltage (Note 3)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.35		-1.1	V
Gate-body leakage current	I _{GSS}	V _{GS} =±10V , V _{DS} =0V			±20	μA
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V , V _{GS} =0V			-1	μA
Drain-source on-states resistance (Note 3)	R _{D(on)}	V _{GS} =-4.5V , I _D =-1A			520	mΩ
		V _{GS} =-2.5V , I _D =-800mA			700	mΩ
		V _{GS} =-1.8V , I _D =-500mA		950		mΩ
Forward transconductance	g _{FS}	V _{DS} =-10V , I _D =-540mA	0.8			S
Dynamic characteristics (Note 4)						
Input capacitance	C _{iss}	V _{DS} =-16V , V _{GS} =0V, f=1MHZ			170	pF
Output capacitance	C _{oss}				25	pF
Reverse transfer capacitance	C _{rss}				15	pF
Switching times (Note 4)						
Turn-on delay time	t _{d(on)}	V _{DD} =-10V , I _D =-200mA V _{GS} =-4.5V , R _G =10Ω		9		nS
Rise time	t _r			5.8		nS
Turn-off delay time	t _{d(off)}			32.7		nS
Fall time	t _r			20.3		nS
Drain-source diode characteristics						
Diode forward voltage (Note 3)	V _{SD}	I _s =-0.5A , V _{GS} =0V			-1.2	V

Note:

3. Pulse Test: Pulse width≤300μs, duty cycle≤0.5%.

4. These parameters have no way to verify.

Dual P-Channel MOSFET

TYPICAL RATING AND CHARACTERISTIC CURVES (CJX3139K-G)

Fig.1 - Output Characteristics

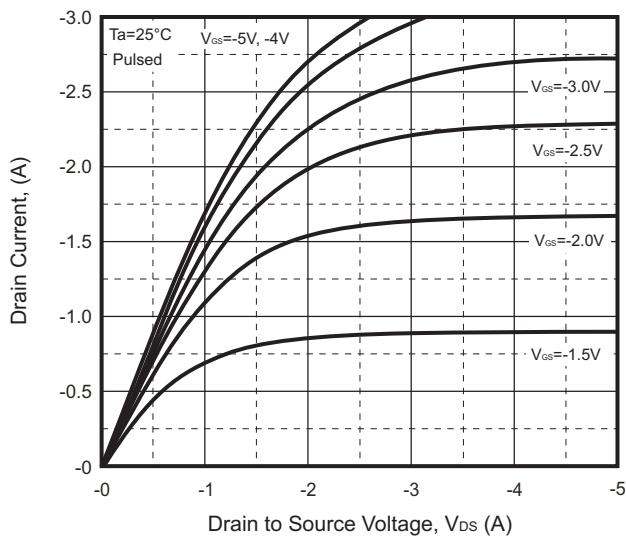


Fig.2 - Transfer Characteristics

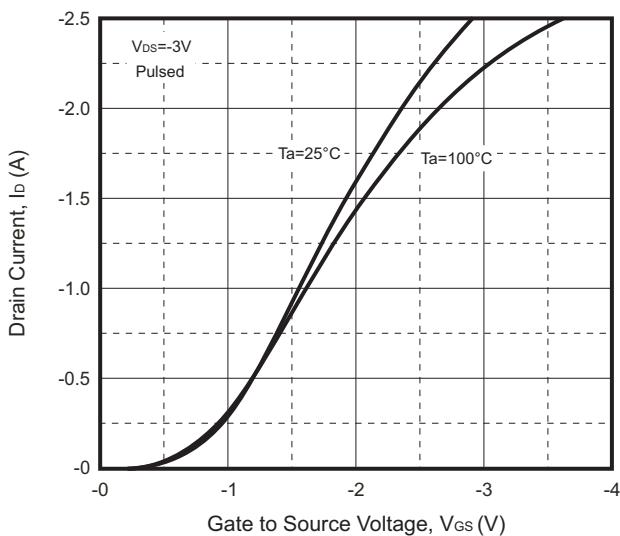


Fig.3 - $R_{DS(ON)}$ — I_D

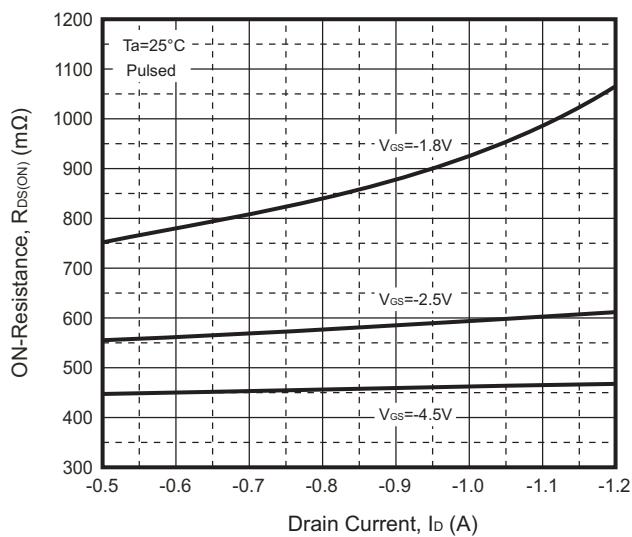


Fig.4 - $R_{DS(ON)}$ — V_{GS}

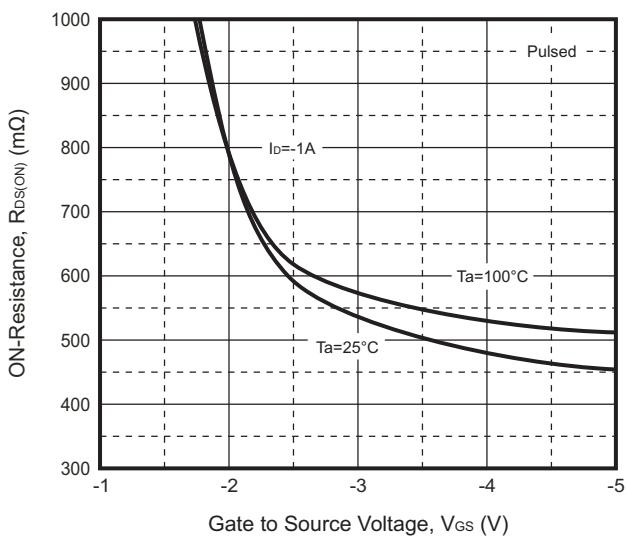


Fig.5 - I_S — V_{SD}

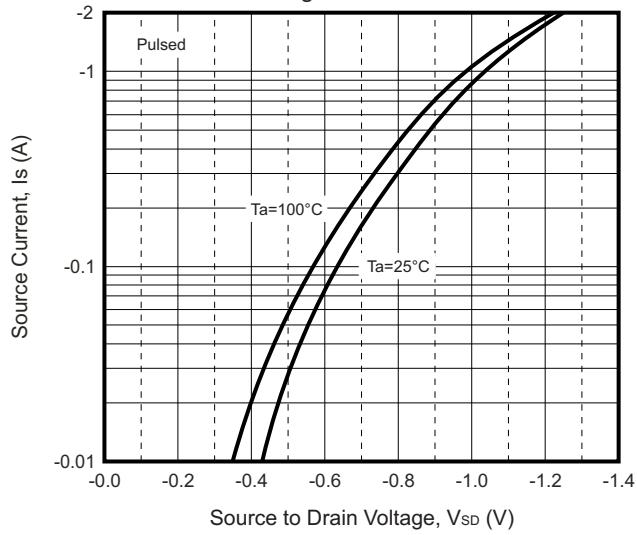
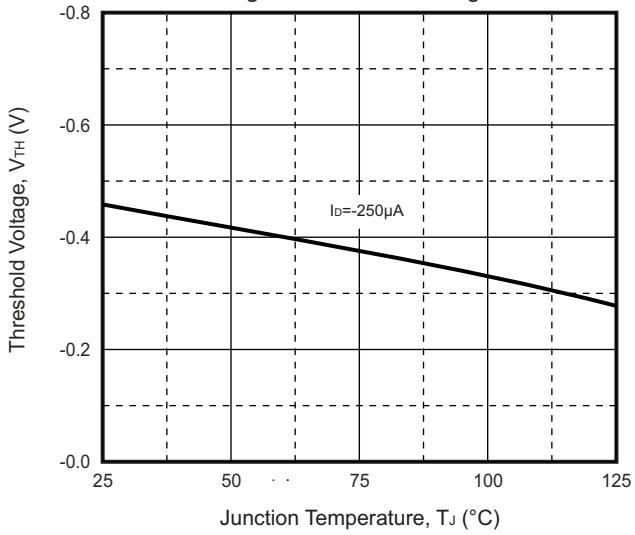


Fig.6 - Threshold Voltage

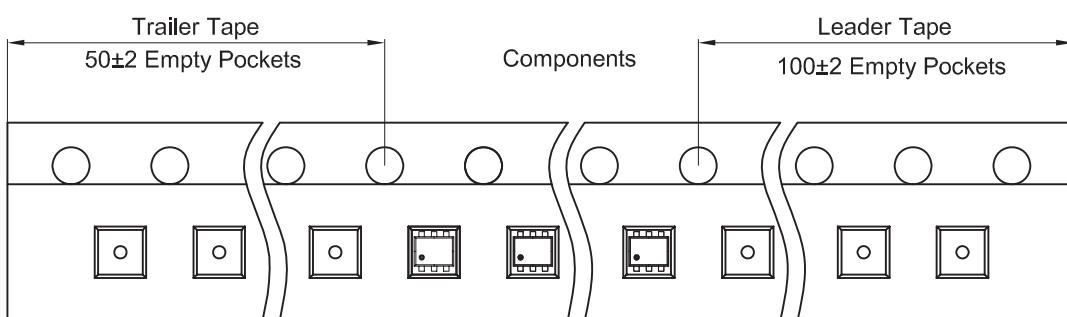
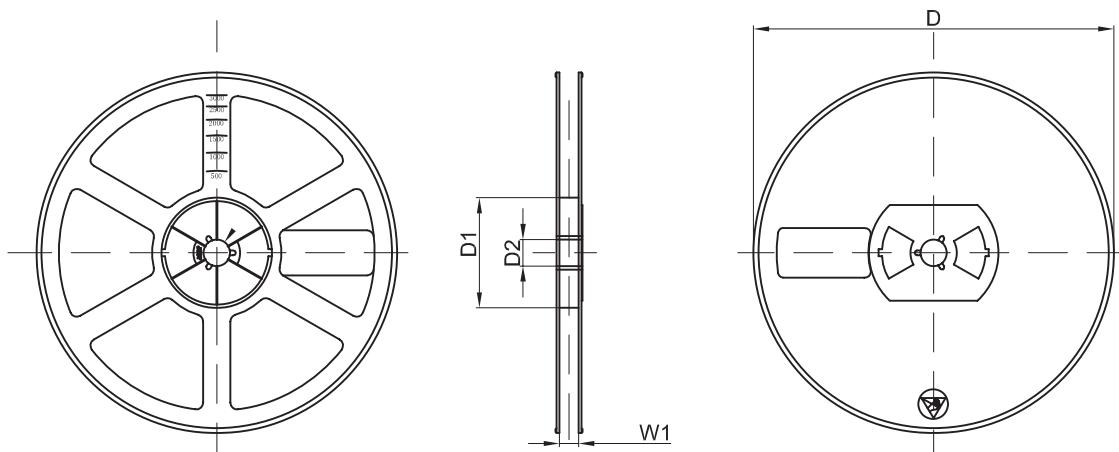
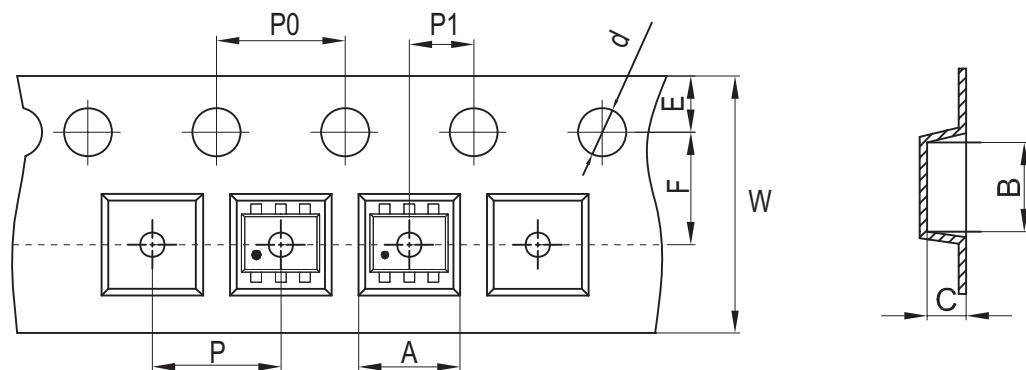


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Dual P-Channel MOSFET

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Reel Taping Specification



SOT-563	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	1.78 \pm 0.10	1.78 \pm 0.10	0.69 \pm 0.10	1.50 \pm 0.10	178 \pm 2.0	54.40 \pm 1.0	13.00 \pm 1.0
	(inch)	0.070 \pm 0.004	0.070 \pm 0.004	0.027 \pm 0.004	0.059 \pm 0.004	7.008 \pm 0.079	2.142 \pm 0.039	0.512 \pm 0.039

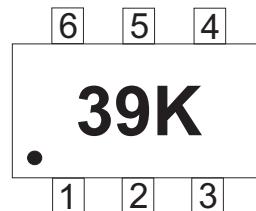
SOT-563	SYMBOL	E	F	P	P0	P1	W	W1
	(mm)	1.75 \pm 0.10	3.50 \pm 0.10	4.00 \pm 0.10	4.00 \pm 0.10	2.00 \pm 0.10	8.00 \pm 0.10	9.50 \pm 1.00
	(inch)	0.069 \pm 0.004	0.138 \pm 0.004	0.158 \pm 0.004	0.158 \pm 0.004	0.079 \pm 0.004	0.315 \pm 0.004	0.374 \pm 0.039

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REV: A

Marking Code

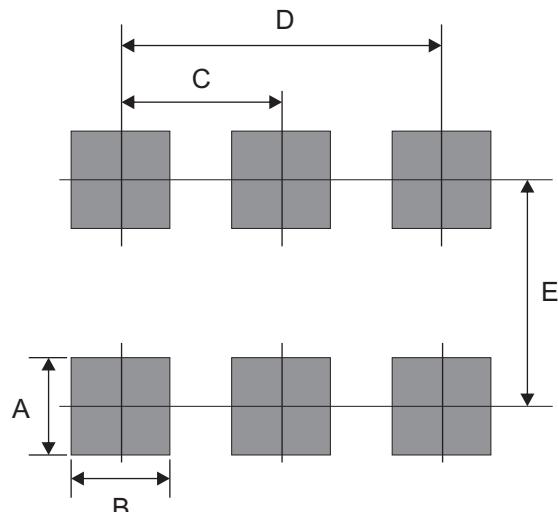
Part Number	Marking Code
CJX3139K-G	39K



Solid dot “●” = Pin 1 indicate.

Suggested PAD Layout

SIZE	SOT-563	
	(mm)	(inch)
A	0.30	0.012
B	0.30	0.012
C	0.50	0.020
D	1.00	0.039
E	1.40	0.055



Note:

- 1.General tolerance: ±0.05mm.
- 2.The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-563	3,000	7